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DIALOG(R) File 351:Derwent WPI

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008496175

WPI Acc No: 1991-000259/ 199101

Preparation of high purity crystalline ammonium-fluoride - takes place with high yield at room temp. by adding ammonia to hydrogen-fluoride soln.

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Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
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DD 281173	A	19900801	DD 327240	A	19890404	199101 B
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Priority Applications (No Type Date): DD 327240 A 19890404

Abstract (Basic): DD 281173 A

Ammonium-fluoride is precipitated by adding ammonia-gas to a concn. soln. of HF. The features are that the HF-soln. or HF containing  $\text{NH}_4\text{F}$ -soln. is neutralised at an operating temp. of 293-308 deg.K. and that the  $\text{NH}_4\text{F}$ -soln., remaining after the  $\text{NH}_4\text{F}$  crystals have been removed, is returned to be used again. The  $\text{NH}_4\text{F}$ -soln. returned for reuse is pref. made up to a HF-concn. of 25-30% while the temp. of the soln. is held at 293-298 deg.K. After this the soln. is reused.

USE/ADVANTAGE - The prod. formed by reaction at low temp. contains very low impurity concns., many at or below the lowest detection level. The reaction can give close to complete conversion of the reactants used. In the production process a second, newly prepared soln. is placed after the main reaction vessel to absorb the small quantity of reactant which failed to react in the main vessel. Reusing the soln. does not decrease the purity of the crystalline material formed. The prod. is used in e.g. semiconductor processing. (3pp Dwg.No.0/0)

Derwent Class: E35; L03; U11

International Patent Class (Additional): C01C-001/16

?s pn=su 379533

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